

## Dual N-Channel Enhancement Mode MOSFET

### 1. Product Information

#### 1.1 Features

- Surface-mounted package
- Low Thermal Resistance

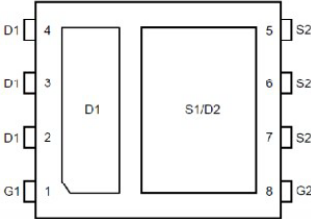
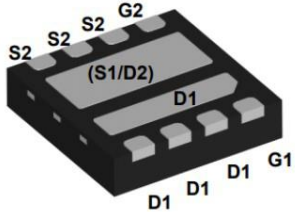
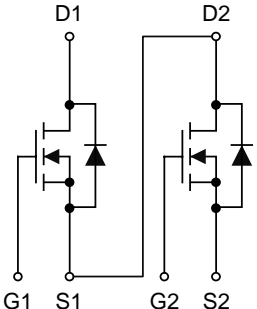
#### 1.2 Applications

- Motor drivers
- DC/DC Converter

#### 1.3 Quick reference

- $BV \geq 30\text{ V}$
- $R_{DS(ON)} \leq 9.5\text{ m}\Omega @ V_{GS} = 10\text{ V}$
- $P_{tot} \leq 20.8\text{ W}$
- $R_{DS(ON)} \leq 12.5\text{ m}\Omega @ V_{GS} = 4.5\text{ V}$
- $I_D \leq 34\text{ A}$

### 2. Pin Description

Pin Description	Simplified Outline	Symbol
	 <p><b>DFN3x3</b></p>	

## 3. Limiting Values

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	Drain-Source Voltage	$T_C=25^{\circ}C$	30	-	V
$V_{GS}$	Gate-Source Voltage	$T_C=25^{\circ}C$	-	$\pm 20$	V
$I_D^*$	Drain Current	$T_C=25^{\circ}C, V_{GS}=10\text{ V}$	-	34	A
$I_{DM}^{*,**,***}$	Pulsed Source Current	$T_C=25^{\circ}C, V_{GS}=10\text{ V}$	-	80	A
$P_{tot}^*$	Total Power Dissipation	$T_C=25^{\circ}C$	-	20.8	W
$T_{stg}$	Storage Temperature		-55	150	$^{\circ}C$
$T_J$	Junction Temperature		-	150	$^{\circ}C$
$I_S$	Diode Forward Current	$T_C=25^{\circ}C$	-	34	A
$R_{\theta JA}^*$	Thermal Resistance-Junction to Ambient		-	62.5	$^{\circ}C/W$
$R_{\theta JC}^*$	Thermal Resistance-Junction to Case		-	6	

**Notes:**

- \* Surface Mounted on 1 in<sup>2</sup> pad area,  $t \leq 10\text{ sec}$
- \*\* Pulse width  $\leq 10\ \mu s$ , duty cycle  $\leq 1\%$
- \*\*\* Limited by bonding wire

## 4. Marking Information

Product Name	Marking
KJ0903CQ	<div style="display: flex; align-items: center;"> <div style="background-color: black; color: white; padding: 2px 5px; margin-right: 10px;">0903 YWWXXX</div> <div>YWW: Date Code</div> </div>

## 5. Ordering Code

Product Name	Package	Reel Size	Tape width	Quantity	Note
KJ0903QD	DFN3x3			5000	

Note: KUIJIEXIN defines "Green" as lead-free (RoHS compliant) and halogen free (Br or Cl does not exceed 900 ppm by weight in homogeneous material and total of Br and Cl does not exceed 1500 ppm by weight; Follow IEC 61249-2-21 and IPC/JEDEC J-STD-020C)

## 6. Electrical Characteristics (T<sub>A</sub>=25°C Unless Otherwise Noted)

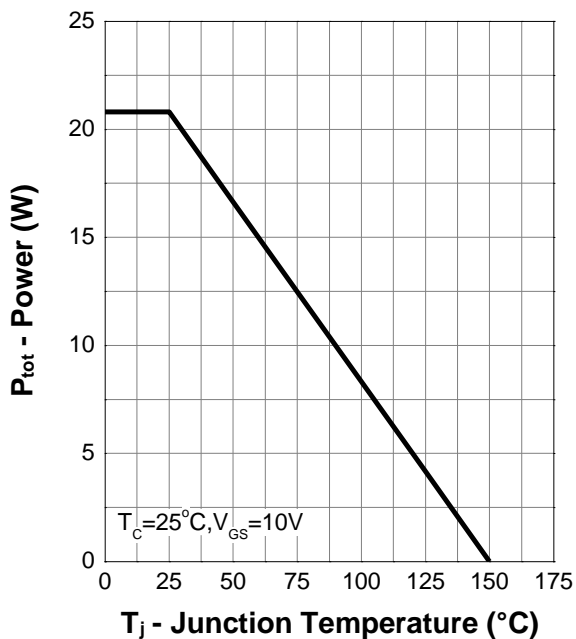
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
B <sub>VDS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0 V, I <sub>D</sub> =250 μA	30	-	-	V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>DS</sub> =250 μA	1.0	-	2.0	V
I <sub>DSS</sub>	Zero Gate Voltage Source Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0 V	-	-	1	μA
		T <sub>J</sub> =85°C	-	-	30	μA
I <sub>GSS</sub>	Gate Leakage Current	V <sub>GS</sub> =±20 V, V <sub>DS</sub> =0 V	-	-	±100	nA
R <sub>DS(ON)</sub> <sup>a</sup>	Drain-Source On-State Resistance	V <sub>GS</sub> =10 V, I <sub>D</sub> =20 A	-	8.5	9.5	mΩ
		V <sub>GS</sub> =4.5 V, I <sub>D</sub> =10 A	-	11.5	12.5	
<b>Diode Characteristics</b>						
V <sub>SD</sub> <sup>a</sup>	Diode Forward Voltage	I <sub>SD</sub> =20 A, V <sub>GS</sub> =0 V	-	-	1.3	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>SD</sub> =20 A, di <sub>SD</sub> /dt=100 A/μs	-	16	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	7	-	nC
<b>Dynamic Characteristics<sup>b</sup></b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0 V, V <sub>DS</sub> =15 V, Frequency=1 MHz	-	918	-	pF
C <sub>oss</sub>	Output Capacitance		-	114	-	
C <sub>rss</sub>	Reverse Transfer Capacitance		-	101	-	
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DS</sub> =15 V, V <sub>GEN</sub> =10 V, R <sub>G</sub> =4.5 Ω, R <sub>L</sub> =0.75 Ω, I <sub>D</sub> =20 A	-	7	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	55	-	
t <sub>d(off)</sub>	Turn-off Delay Time		-	19	-	
t <sub>f</sub>	Turn-off Fall Time		-	23	-	
<b>Gate Charge Characteristics<sup>b</sup></b>						
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> =10 V, V <sub>DS</sub> =15 V, I <sub>DS</sub> =20 A	-	20	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	3.6	-	
Q <sub>gd</sub>	Gate-Drain Charge		-	3.9	-	

**Notes:**

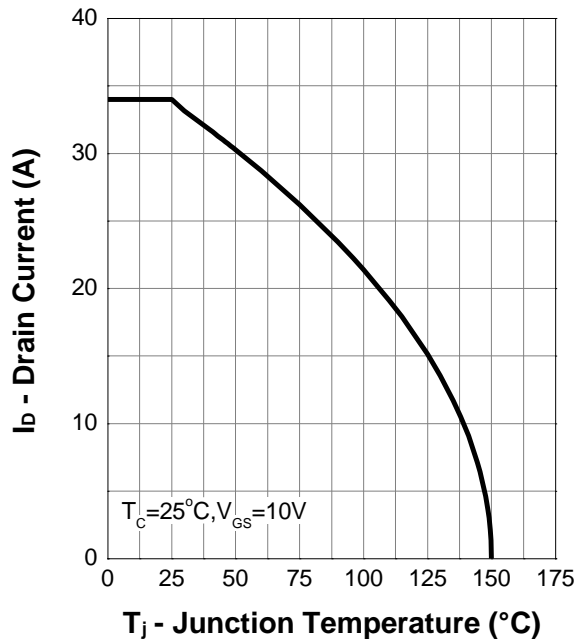
- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%
- Guaranteed by design, not subject to production testing

## 7. Typical Characteristics (Cont.)

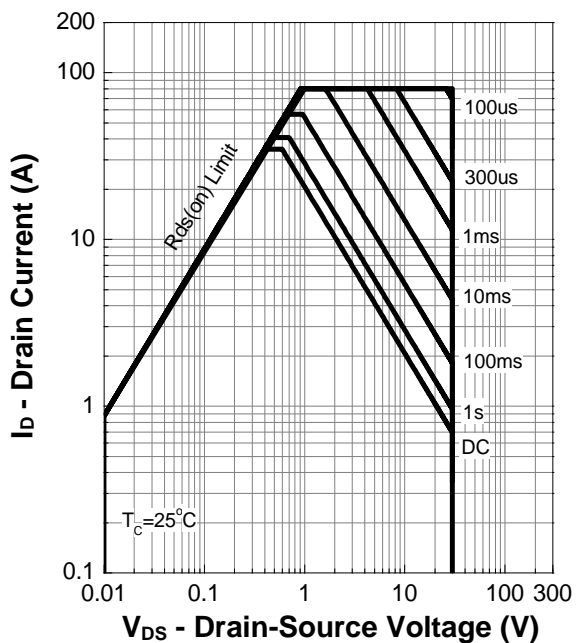
**Power Capability**



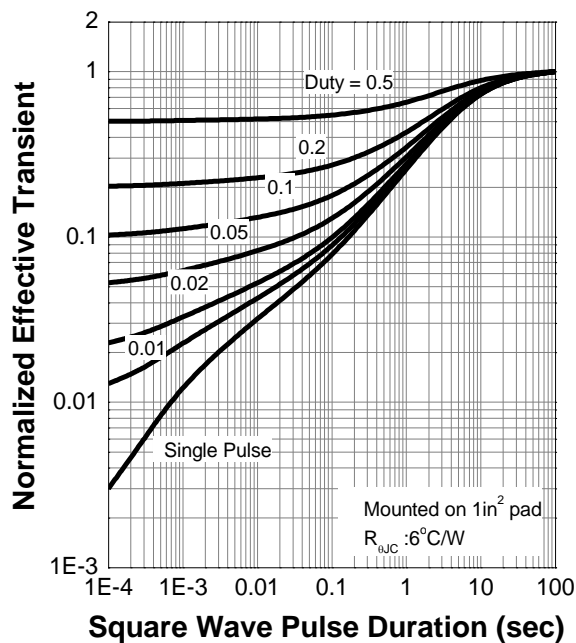
**Current Capability**



**Safe Operating Area**

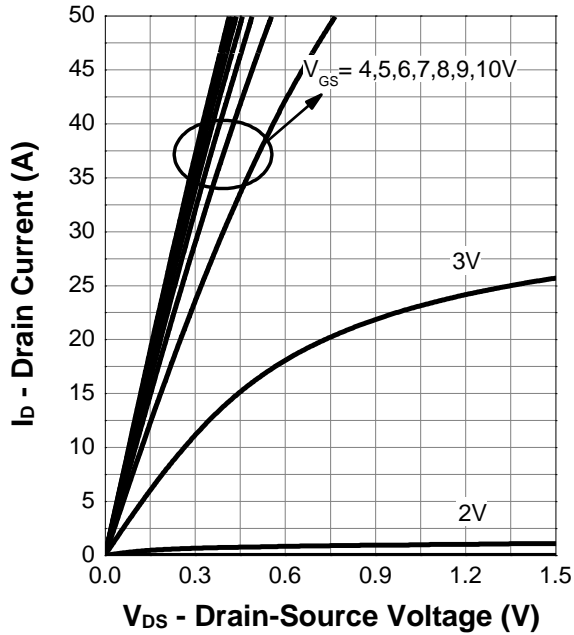


**Transient Thermal Impedance**

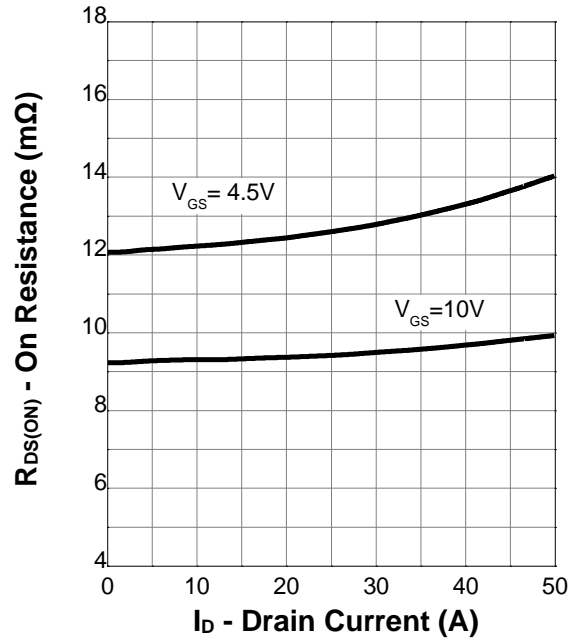


## 7. Typical Characteristics (Cont.)

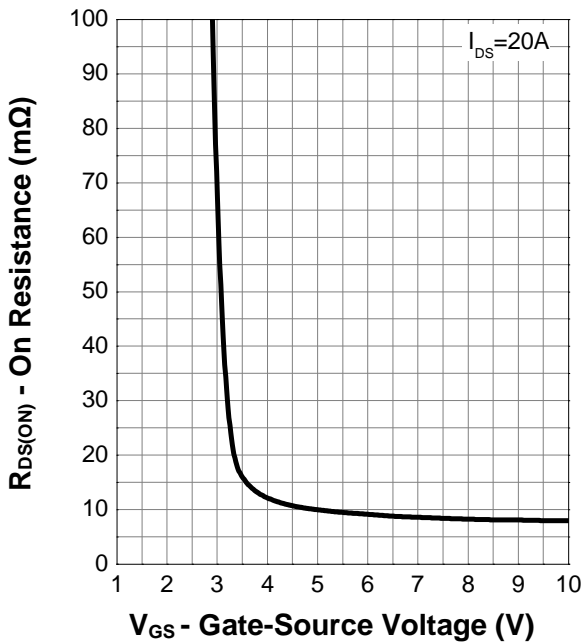
Output Characteristics



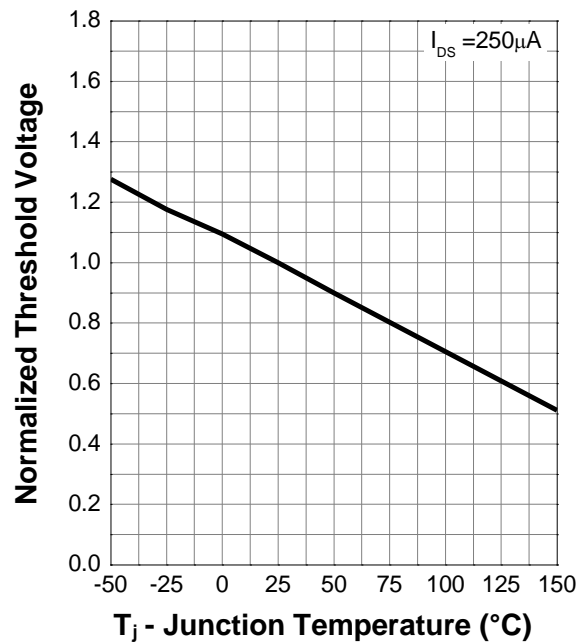
On Resistance



Transfer Characteristics

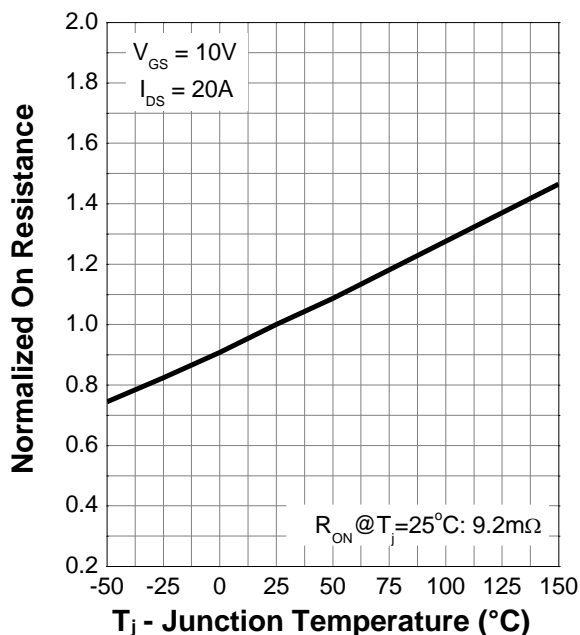


Normalized Threshold Voltage

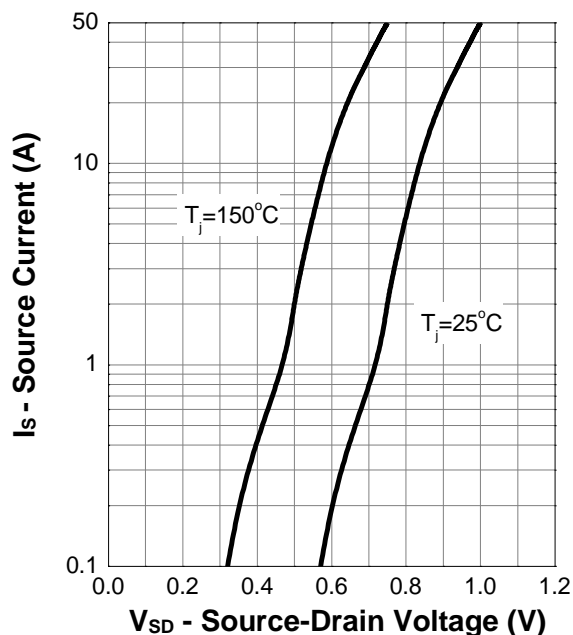


## 7. Typical Characteristics (Cont.)

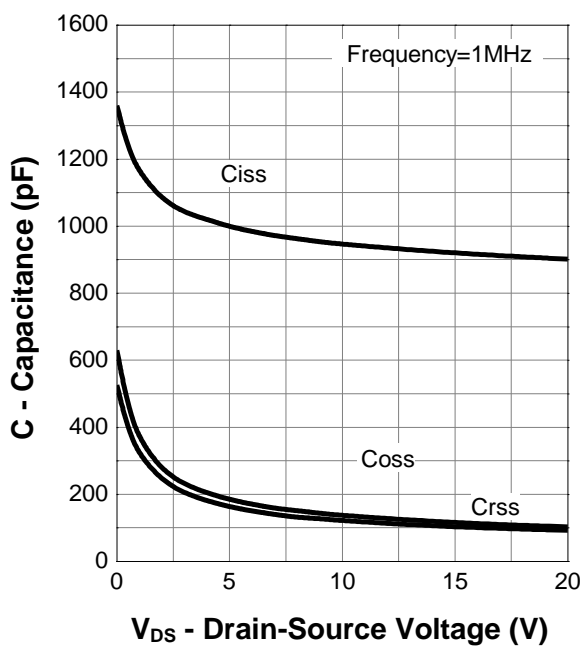
Normalized On Resistance



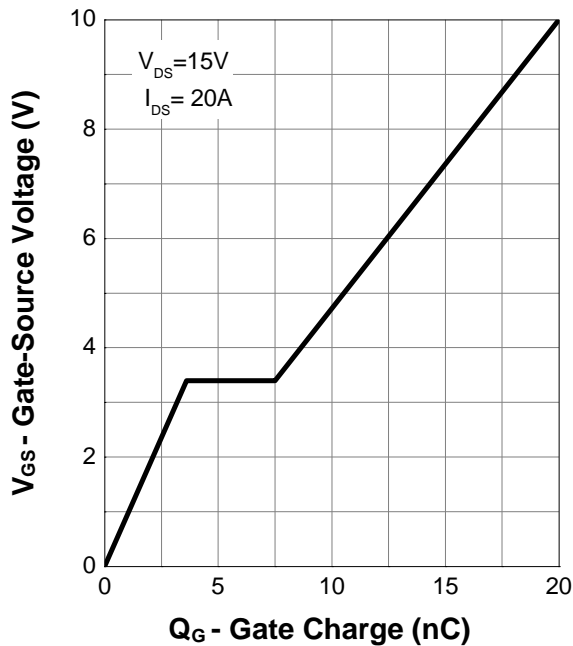
Diode Forward Current



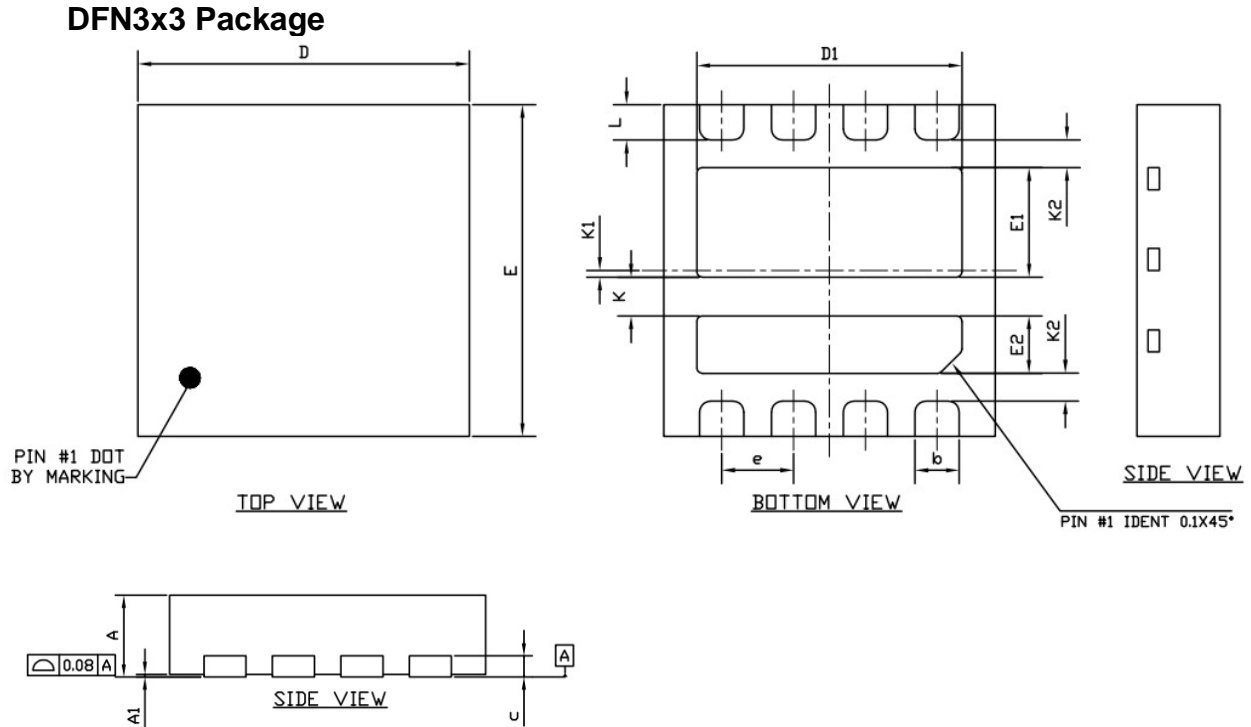
Capacitance



Gate Charge



## 8. Package Dimensions



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.75	0.80	0.028	0.030	0.032
A1	0.00	---	0.05	0.000	---	0.002
c	0.203 REF.			0.008 REF.		
b	0.35	0.40	0.45	0.014	0.016	0.018
D	2.90	3.00	3.10	0.114	0.118	0.122
D1	2.30	2.40	2.50	0.090	0.094	0.098
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	0.89	0.99	1.09	0.035	0.039	0.043
E2	0.42	0.52	0.62	0.016	0.020	0.024
e	0.65 BSC			0.026 BSC		
L	0.27	0.32	0.37	0.011	0.013	0.015
K	0.35 REF.			0.014 REF.		
K1	0.06 REF.			0.002 REF.		
K2	0.25 REF.			0.010 REF.		